

# Max Kneiß

## List of Publications by Year in descending order

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29  
papers

893  
citations

516710

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h-index

454955

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times ranked

1007  
citing authors

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Structural and Elastic Properties of $\hat{1}\pm\hat{a}\text{(Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ Thin Films on (11.0) $\text{Al}_{2}\text{O}_{3}$ Substrates for the Entire Composition Range. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2000394.  | 1.5 | 18        |
| 2  | Epitaxial Growth of $\text{Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ Layers and Superlattice Heterostructures up to $x=0.48$ on Highly Conductive Al-Doped ZnO Thin-Film Templates by Pulsed Laser Deposition. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2000359.   | 1.5 | 7         |
| 3  | Realization of highly rectifying Schottky barrier diodes and <i>pn</i> heterojunctions on $\text{In}_{2}\text{O}_{3}$ -Ga $_{2}\text{O}_{3}$ by overcoming the conductivity anisotropy. <i>Journal of Applied Physics</i> , 2021, 130, .  | 2.5 | 24        |
| 4  | Strain states and relaxation for $\alpha\text{-Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ thin films on prismatic planes of $\alpha\text{-Al}_{2}\text{O}_{3}$ in the full composition range: Fundamental difference of a- and m-epitaxial planes in the manifestation of shear strain and lattice tilt. <i>Journal of Materials Research</i> , 2021, 36, 4816-4831. | 2.6 | 9         |
| 5  | Epitaxial growth of rhombohedral $\hat{1}^{2-}$ and cubic $\hat{1}^{3-}$ -CuI. <i>Journal of Crystal Growth</i> , 2021, 570, 126218.  | 1.5 | 6         |
| 6  | Method of full polarization control of microwave fields in a scalable transparent structure for spin manipulation. <i>Journal of Applied Physics</i> , 2020, 128, .   | 2.5 | 4         |
| 7  | Annealing Effects on the Band Alignment of ALD $\text{SiO}_{2}$ on $(\text{In}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ for $x = 0.25\text{--}0.74$ . <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 045001.  | 1.8 | 0         |
| 8  | Changes in band alignment during annealing at 600 $^{\circ}\text{C}$ of ALD $\text{Al}_{2}\text{O}_{3}$ on $(\text{In}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ for $x = 0.25\text{--}0.74$ . <i>Journal of Applied Physics</i> , 2020, 127, 105701.   | 2.5 | 6         |
| 9  | Solubility limit and material properties of a $\hat{1}^{2-}(\text{Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ thin film with a lateral cation gradient on $(00.1)\text{Al}_{2}\text{O}_{3}$ by tin-assisted PLD. <i>APL Materials</i> , 2020, 8, 021103.  | 5.1 | 26        |
| 10 | A Review of the Segmented-Target Approach to Combinatorial Material Synthesis by Pulsed-Laser Deposition. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900626.  | 1.5 | 26        |
| 11 | Band Offsets at $\hat{1}^{2-}(\text{Al},\text{In})_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}/\text{MgO}$ Interfaces. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 8879-8885.  | 8.0 | 14        |
| 12 | Growth, structural and optical properties of coherent $\text{In}_{2}\text{O}_{3}/\text{Ga}_{2}\text{O}_{3}$ quantum well superlattice heterostructures. <i>APL Materials</i> , 2020, 8, .   | 5.1 | 24        |
| 13 | Control of phase formation of $(\text{Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ thin films on c-plane $\text{Al}_{2}\text{O}_{3}$ . <i>Journal Physics D: Applied Physics</i> , 2020, 53, 485105.   | 2.8 | 24        |
| 14 | Valence band offsets for ALD $\text{SiO}_{2}$ and $\text{Al}_{2}\text{O}_{3}$ on $(\text{In}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ for $x = 0.25\text{--}0.74$ . <i>APL Materials</i> , 2019, 7, .  | 5.1 | 14        |
| 15 | Band Alignment of Atomic Layer Deposited $\text{SiO}_{2}$ and $\text{Al}_{2}\text{O}_{3}$ on $(\text{Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ for $x = 0.2\text{--}0.65$ . <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, P351-P356.  | 1.8 | 12        |
| 16 | Band Offsets of Insulating & Semiconducting Oxides on $(\text{Al}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ . <i>ECS Transactions</i> , 2019, 92, 79-88.  | 0.5 | 6         |
| 17 | Heteroepitaxial growth of $\hat{1}^{\pm}$ , $\hat{1}^{2-}$ , $\hat{1}^{3-}$ and $\hat{1}^{2-}$ -Ga $_{2}\text{O}_{3}$ phases by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2019, 510, 76-84.  | 1.5 | 59        |
| 18 | Structural, optical, and electrical properties of orthorhombic $\hat{1}^{2-}(\text{In}_{x}\text{Ga}_{1-x}\text{)}_{2}\text{O}_{3}$ thin films. <i>APL Materials</i> , 2019, 7, .  | 5.1 | 34        |

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|----|--|------|-----------|
| 19 | Effect of Annealing on the Band Alignment of ALD SiO <sub>2</sub> on (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> for x = 0.2 - 0.65. ECS Journal of Solid State Science and Technology, 2019, 8, P751-P756.       | 1.8  | 6         |
| 20 | Epitaxial stabilization of single phase $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ thin films up to $x = 0.28$ on c-sapphire and $\text{In}_x\text{Ga}_{1-x}\text{O}_3(001)$ templates by tin-assisted VCCS-PLD. APL Materials, 2019, 7, . | 5.1  | 38        |
| 21 | Epitaxial $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ thin films and heterostructures grown by tin-assisted VCCS-PLD. APL Materials, 2019, 7, .   | 5.1  | 30        |
| 22 | Highly transparent conductors for optical and microwave access to spin-based quantum systems. Npj Quantum Information, 2019, 5, .  | 6.7  | 8         |
| 23 | Tin-assisted heteroepitaxial PLD-growth of $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ thin films with high crystalline quality. APL Materials, 2019, 7, .  | 5.1  | 98        |
| 24 | Suppression of Grain Boundary Scattering in Multifunctional p-Type Transparent $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ Thin Films due to Interface Tunneling Currents. Advanced Materials Interfaces, 2018, 5, 1701411.                 | 3.7  | 26        |
| 25 | Combinatorial Material Science and Strain Engineering Enabled by Pulsed Laser Deposition Using Radially Segmented Targets. ACS Combinatorial Science, 2018, 20, 643-652.   | 3.8  | 21        |
| 26 | Transparent flexible thermoelectric material based on non-toxic earth-abundant p-type copper iodide thin film. Nature Communications, 2017, 8, 16076.  | 12.8 | 233       |
| 27 | Room-temperature Domain-epitaxy of Copper Iodide Thin Films for Transparent CuI/ZnO Heterojunctions with High Rectification Ratios Larger than 109. Scientific Reports, 2016, 6, 21937.  | 3.3  | 91        |
| 28 | From high- $T_c$ superconductors to highly correlated Mott insulatorsâ€”25 years of pulsed laser deposition of functional oxides in Leipzig. Semiconductor Science and Technology, 2015, 30, 024003.                                   | 2.0  | 7         |
| 29 | Modeling the electrical transport in epitaxial undoped and Ni-, Cr-, and W-doped TiO <sub>2</sub> anatase thin films. Applied Physics Letters, 2014, 105, 062103.  | 3.3  | 20        |